

# KBP2005 THRU KBP210

## SINGLE-PHASE SILICON BRIDGE RECTIFIER

REVERSE VOLTAGE: 50 to 1000 V

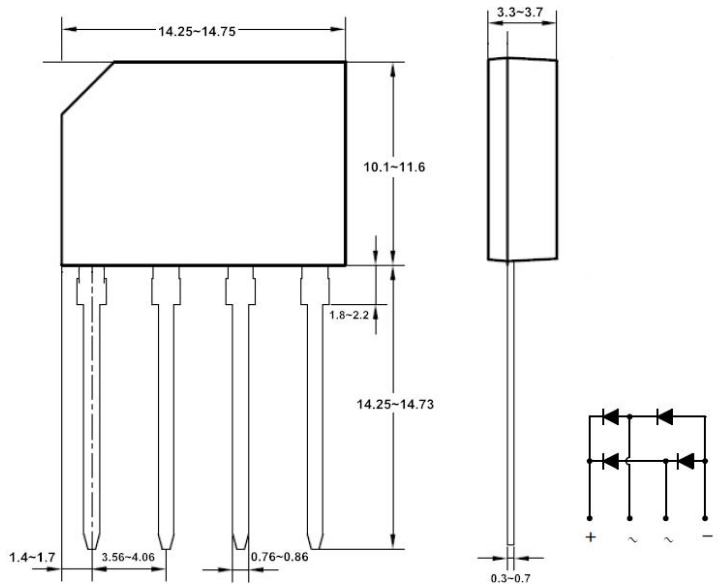
FORWARD CURRENT: 2 A

### Features

- Reliable low cost construction utilizing molded plastic technique
- Ideal for printed circuit board
- Low forward voltage drop
- Low reverse leakage current
- High surge current capability

### Mechanical Data

- Case: Molded plastic, KBP
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Leads solderable per MIL-STD-202 method 208 guaranteed
- Mounting position: Any



Dimensions in millimeters

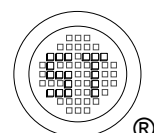
### Absolute Maximum Ratings and Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbols	KBP 2005	KBP 201	KBP 202	KBP 204	KBP 206	KBP 208	KBP 210	Units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current .375" (9.5 mm) Lead Length at $T_A = 50\text{ }^\circ\text{C}$	$I_{(AV)}$	2							A
Peak Forward Surge Current, 8.3 ms Single Half-Sine -Wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	55							A
Maximum Forward Voltage at 2 A DC and 25 °C	$V_F$	1.1							V
Maximum Reverse Current $T_A = 25\text{ }^\circ\text{C}$ at Rated DC Blocking Voltage $T_A = 100\text{ }^\circ\text{C}$	$I_R$	5 500							$\mu\text{A}$
Typical Junction Capacitance <sup>1)</sup>	$C_J$	25							pF
Typical Thermal Resistance <sup>2)</sup>	$R_{\theta JA}$	40							$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{Stg}$	-55 to +150							$^\circ\text{C}$

<sup>1)</sup> Measured at 1 MHz and applied reverse voltage of 4 VDC.

<sup>2)</sup> Thermal resistance junction to Case, Lead and Ambient.



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